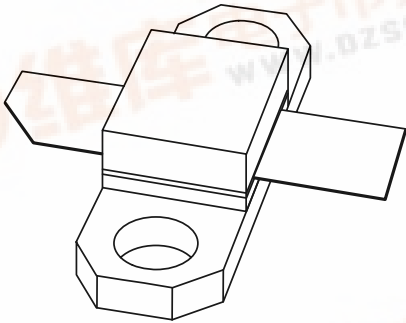


DISCRETE SEMICONDUCTORS

DATA SHEET



BLF1046

UHF power LDMOS transistor

Preliminary specification
Supersedes data of 1999 Nov 02

2000 Feb 02

UHF power LDMOS transistor

BLF1046

FEATURES

- High power gain
- Easy power control
- Excellent ruggedness
- Source on underside eliminates DC isolators, reducing common mode inductance
- Designed for broadband operation (HF to 1 GHz).

APPLICATIONS

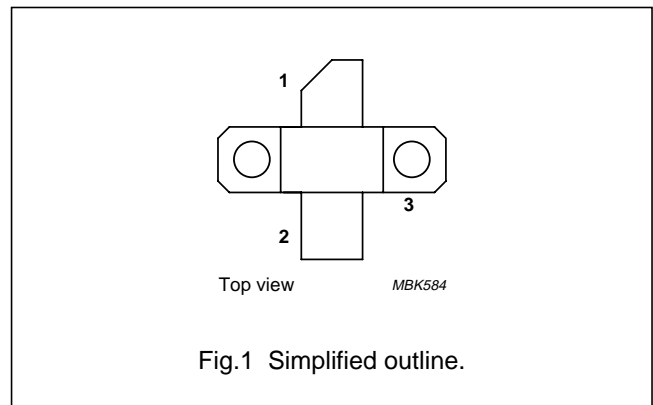
- Communication transmitter applications in the UHF frequency range.

DESCRIPTION

Silicon N-channel enhancement mode lateral D-MOS transistor encapsulated in a 2-lead flange package (SOT467C) with a ceramic cap. The common source is connected to the mounting flange.

PINNING - SOT467C

PIN	DESCRIPTION
1	drain
2	gate
3	source, connected to flange



QUICK REFERENCE DATA

RF performance at $T_h = 25\text{ }^\circ\text{C}$ in a common source test circuit.

MODE OF OPERATION	f (MHz)	V _{DS} (V)	P _L (W)	G _p (dB)	η_D (%)	d _{im} (dBc)
CW, class-AB (2-tone)	$f_1 = 960; f_2 = 960.1$	26	45 (PEP)	>14	>35	≤ -28
CW, class-AB (1-tone)	960	26	45	>14	>45	-

CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage	–	65	V
V_{GS}	gate-source voltage	–	± 20	V
I_D	drain current (DC)	–	4.5	A
T_{stg}	storage temperature	–65	+150	$^{\circ}\text{C}$
T_j	junction temperature	–	200	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-h}$	thermal resistance from junction to heatsink	$T_h = 25\text{ }^{\circ}\text{C}$, $P_{dis} = 97\text{ W}$; note 1	1.2	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink		0.6	K/W

Note

1. Determined under specified RF operating conditions, based on maximum peak junction temperature.

CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0$; $I_D = 0.7\text{ mA}$	65	–	–	V
V_{GSth}	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 70\text{ mA}$	4	–	5	V
I_{DSS}	drain-source leakage current	$V_{GS} = 0$; $V_{DS} = 26\text{ V}$	–	–	1	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GSth} + 9\text{ V}$; $V_{DS} = 10\text{ V}$	12.5	–	–	A
I_{GSS}	gate leakage current	$V_{GS} = \pm 20\text{ V}$; $V_{DS} = 0$	–	–	125	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}$; $I_D = 3.5\text{ A}$	–	2	–	S
R_{DSon}	drain-source on-state resistance	$V_{GS} = V_{GSth} + 9\text{ V}$; $I_D = 3.5\text{ A}$	–	300	–	$\text{m}\Omega$
C_{is}	input capacitance	$V_{GS} = 0$; $V_{DS} = 26\text{ V}$; $f = 1\text{ MHz}$	–	46	–	pF
C_{os}	output capacitance	$V_{GS} = 0$; $V_{DS} = 26\text{ V}$; $f = 1\text{ MHz}$	–	37	–	pF
C_{rs}	feedback capacitance	$V_{GS} = 0$; $V_{DS} = 26\text{ V}$; $f = 1\text{ MHz}$	–	1.5	–	pF

APPLICATION INFORMATIONRF performance in a common source class-AB circuit. $T_h = 25\text{ }^{\circ}\text{C}$; $R_{th\ mb-h} = 0.6\text{ K/W}$, unless otherwise specified.

MODE OF OPERATION	f (MHz)	V_{DS} (V)	P_L (W)	G_p (dB)	η_D (%)	d_{im} (dBc)
CW, class-AB (2-tone)	$f_1 = 960$; $f_2 = 960.1$	26	45 (PEP)	>14	>35	≤ -28
CW, class-AB (1-tone)	960	26	45	>14	>45	–

Ruggedness in class-AB operationThe BLF1046 is capable of withstanding a load mismatch corresponding to $VSWR = 10 : 1$ through all phases under the following conditions: $V_{DS} = 26\text{ V}$; $f = 960\text{ MHz}$ at rated load power.

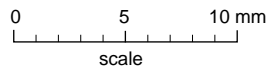
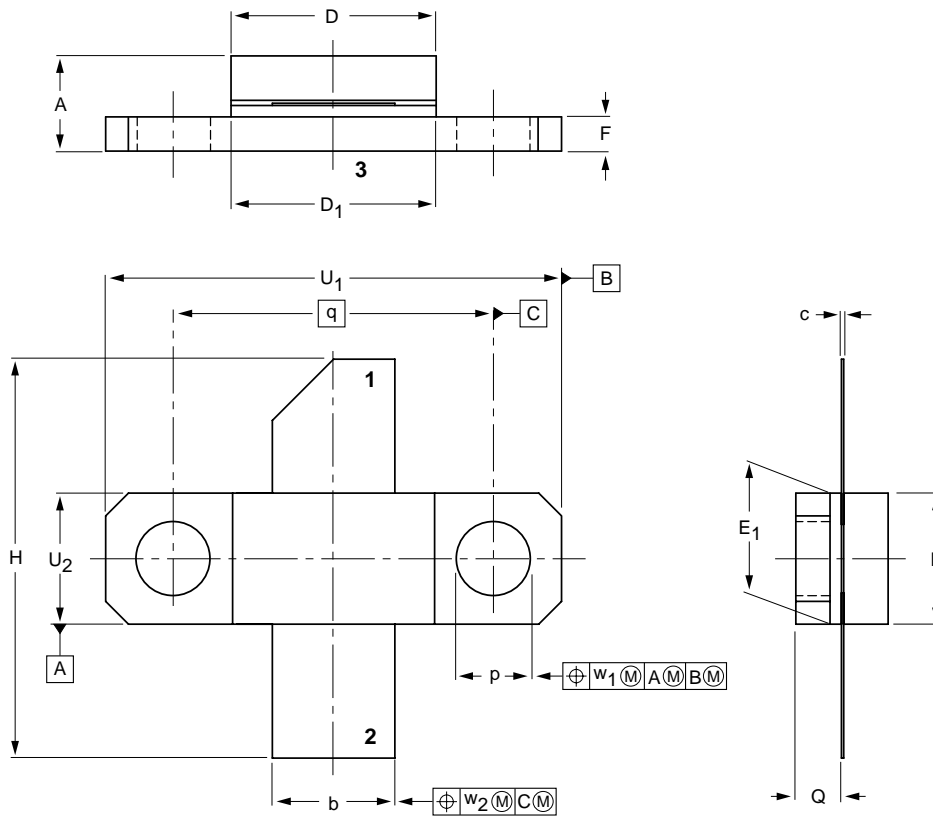
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PACKAGE OUTLINE

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads

SOT467C



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₁	E	E ₁	F	H	p	Q	q	U ₁	U ₂	w ₁	w ₂
mm	4.67 3.94	5.59 5.33	0.15 0.10	9.25 9.04	9.27 9.02	5.92 5.77	5.97 5.72	1.65 1.40	18.54 17.02	3.43 3.18	2.21 1.96	14.27	20.45 20.19	5.97 5.72	0.25	0.51
inch	0.184 0.155	0.220 0.210	0.006 0.004	0.364 0.356	0.365 0.355	0.233 0.227	0.235 0.225	0.065 0.055	0.73 0.67	0.135 0.125	0.087 0.077	0.562	0.805 0.795	0.235 0.225	0.010	0.020

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT467C						99-12-06 99-12-28

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

UHF power LDMOS transistor

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NOTES

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